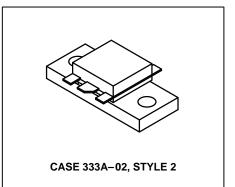
The RF Line NPN Silicon RF Power Transistor

The MRF6414 is designed for 26 volt UHF large signal, common emitter, class AB linear amplifier applications.

- Specified 26 Volt, 960 MHz Characteristics Output Power = 50 Watts Minimum Gain = 8.5 dB @ 960 MHz, Class AB Minimum Efficiency = 50% @ 960 MHz, 50 Watts
- Silicon Nitride Passivated
- Gold Metallized, Emitter Ballasted for Long Life and Resistance to Metal Migration
- Circuit Board Photomaster Available by Ordering Document MRF6414PHT/D from Motorola Literature Distribution.



50 W, 960 MHz RF POWER TRANSISTOR NPN SILICON



MAXIMUM RATINGS

Rating			Value		Unit
Collector-Emitter Voltage		VCEO	28		Vdc
Collector-Base Voltage		V _{CBO}	65		Vdc
Emitter-Base Voltage		V _{EBO}	4		Vdc
Collector-Current — Continuous		IC	6		Adc
Total Device Dissipation @ T _C = 25°C Derate above 25°C		PD	134 0.77		Watts W/°C
Storage Temperature Range		T _{stg}	-65 to +150		°C
THERMAL CHARACTERISTICS					
Characteristic		Symbol	Max		Unit
Thermal Resistance, Junction to Case		R _θ JC	1.3		°C/W
ELECTRICAL CHARACTERISTICS (T _C = 25° C unless otherwi	se noted)				
Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	•			•	
Collector–Emitter Breakdown Voltage ($I_C = 20 \text{ mAdc}, I_B = 0$)	V(BR)CEO	28	—	-	Vdc
Collector–Base Breakdown Voltage ($I_C = 20 \text{ mAdc}, I_E = 0$)	V(BR)CBO	65	—	-	Vdc
Emitter–Base Breakdown Voltage ($I_E = 10 \text{ mAdc}, I_C = 0$)	V(BR)EBO	4	_	-	Vdc
Collector–Emitter Leakage Current (V _{CE} = 30 Vdc, R _{BE} = 75 Ω)	ICER	—	—	10	mAdc
ON CHARACTERISTICS	•				·
DC Current Gain (I _{CE} = 1 Adc, V _{CE} = 5 Vdc)	hFF	30	_	120	_



ELECTRICAL CHARACTERISTICS — continued ($T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
DYNAMIC CHARACTERISTICS					
Output Capacitance (V_{CB} = 26 Vdc, I _E = 0, f = 1 MHz) (1)	C _{ob}	—	45	—	pF
FUNCTIONAL TESTS					
Common–Emitter Amplifier Power Gain (V _{CC} = 26 Vdc, P _{out} = 50 W, I _{CQ} = 200 mA, f = 960 MHz)	G _{pe}	8.5	_	_	dB
Collector Efficiency (V _{CC} = 26 Vdc, P_{out} = 50 W, I _{CQ} = 200 mA, f = 960 MHz)	η	50	55	_	%
Output Mismatch Stress (V _{CC} = 26 Vdc, P _{OUt} = 50 W, I _{CQ} = 200 mA, f = 960 MHz) VSWR = 3:1; all phase angles at frequency of test	Ψ	No Degradation in Output Power			

(1) For information only. It is not measurable in MRF6414 because of internal matching network.

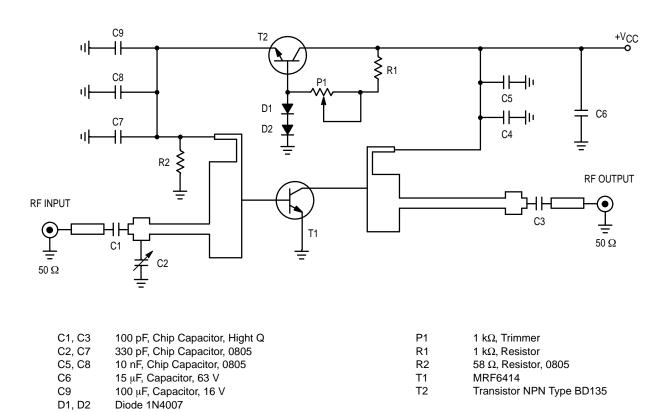


Figure 1. 960 MHz Test Circuit Schematic

TYPICAL CHARACTERISTICS

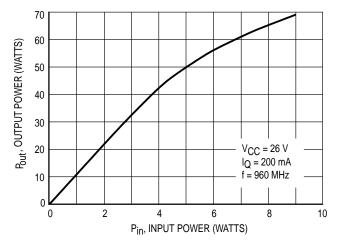


Figure 2. Output Power versus Input Power (Typical)

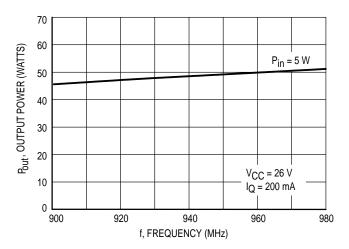


Figure 3. Output Power versus Frequency

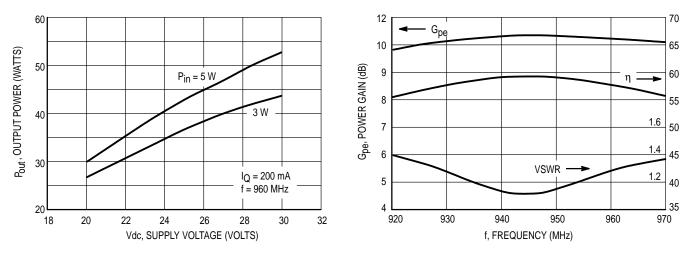


Figure 4. Output Power versus Supply Voltage

Figure 5. Typical Broadband Amplifier

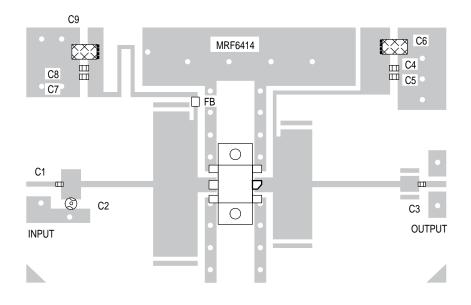
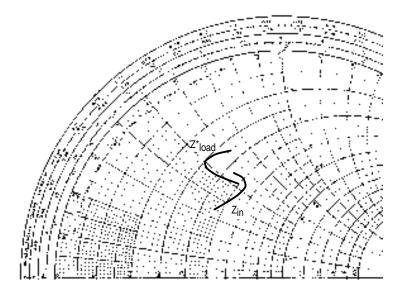


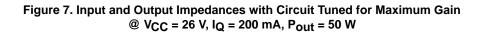
Figure 6. 960 MHz Test Circuit Components Layout



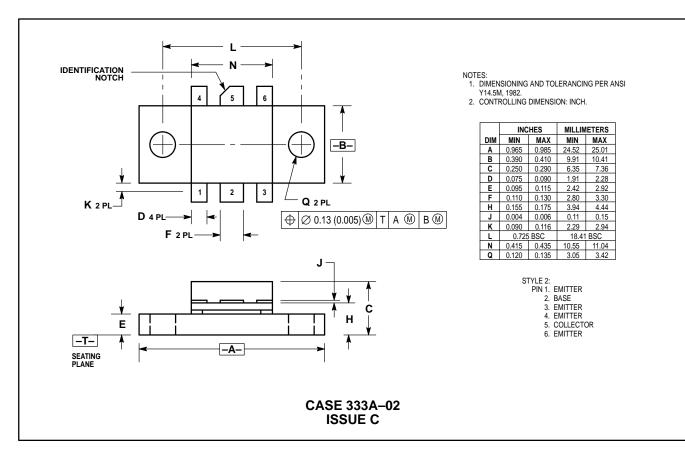
Normalized to 10 Ω

f MHz	Z _{in} Ohms	Z _{OL} * Ohms
900	4.4 + j4.6	4.7 + j4.7
935	5.1 + j4.8	4.0 + j3.9
960	5.4 + j3.6	3.7 + j4.5
980	4.7 + j2.5	3.4 + j4.7

Z_{OL}*: Conjugate of optimum load impedance into which the device operates at a given output power, voltage, current and frequency.



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